



DZT951

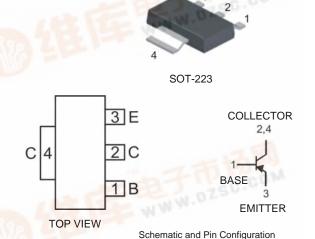
PNP SURFACE MOUNT TRANSISTOR

Features

- **Epitaxial Planar Die Construction**
- Complementary NPN Type Available (DZT851)
- Ideally Suited for Automated Assembly Processes
- Ideal for Medium Power Switching or Amplification Applications
- Lead Free By Design/RoHS Compliant (Note 1)
- "Green" Device (Note 2)

Mechanical Data

- Case: SOT-223
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminals: Finish Matte Tin annealed over Copper Leadframe (Lead Free Plating). Solderable per MIL-STD-202, Method 208
- Marking Information: See Page 3
- Ordering Information: See Page 3
- Weight: 0.115 grams (approximate)



Maximum Ratings @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	-100	V
Collector-Emitter Voltage	V _{CEO}	-60	V
Emitter-Base Voltage	V _{EBO}	-6	V
Continuous Collector Current	lc	-5	A
Power Dissipation	P _{tot}	1(Note 3) 3(Note 4)	W
Operating and Storage Temperature Range	T_j , T_{STG}	-55 to +150	°C

Notes:

- No purposefully added lead. 1.
- Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php. 2
- Device mounted on FR-4 PCB, pad layout as shown on page 4.

 The power which can be dissipated, assuming the device is mounted in a typical manner on a PCB with copper equal to 4 square inch minimum.





Electrical Characteristics $@T_A = 25$ °C unless otherwise specified

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition		
OFF CHARACTERISTICS								
Collector-Base Breakdown Voltage	V _{(BR)CBO}	-100	_	_	V	$I_C = -100 \mu A, I_E = 0$		
Collector-Emitter Breakdown Voltage	V _{(BR)CEO}	-60	_	_	V	$I_C = -10 \text{mA*}, I_B = 0$		
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	-6	_	—	V	$I_E = -100 \mu A, I_C = 0$		
Collector Cutoff Current	I _{CBO}	_	_	-50 -1	nA μA	$V_{CB} = -80V, I_{E} = 0$ $V_{CB} = -80V, I_{E} = 0, T_{A} = 100^{\circ}C$		
Emitter Cutoff Current	I _{EBO}	_	_	-10	nA	$V_{EB} = -6V, I_{C} = 0$		
ON CHARACTERISTICS								
Collector-Emitter Saturation Voltage			-20 -85 -155 -370	-50 -140 -210 -460	mV	$\begin{split} I_C &= -100 \text{mA}, \ I_B = -10 \text{mA}^* \\ I_C &= -1\text{A}, \ I_B = -100 \text{mA}^* \\ I_C &= -2\text{A}, \ I_B = -200 \text{mA}^* \\ I_C &= -5\text{A}, \ I_B = -500 \text{mA}^* \end{split}$		
Base-Emitter Saturation Voltage	V _{BE(SAT)}	_	-1080	-1240	mV	$I_C = -5A$, $I_B = -500 \text{mA}^*$		
Base-Emitter Turn-On Voltage	V _{BE(ON)}	_	-935	-1070	mV	$I_{CE} = -5A$, $V_{CE} = -1V^*$		
DC Current Gain		100 100 75 10	200 200 90 25	300 — —	_	$\begin{split} I_C &= -10 \text{mA}, \ V_{CE} = -1 \text{V}^* \\ I_C &= -2 \text{A}, \ V_{CE} = -1 \text{V}^* \\ I_C &= -5 \text{A}, \ V_{CE} = -1 \text{V}^* \\ I_C &= -10 \text{A}, \ V_{CE} = -1 \text{V}^* \end{split}$		
SMALL SIGNAL CHARACTERISTICS				_				
Current Gain-Bandwidth Product	f _T	_	120	_	MHz	$I_C = -100 \text{mA}, V_{CE} = -10 \text{V},$ f = 50MHz		
Output Capacitance			74	_	pF	$V_{CB} = -10V$, $f = 1MHz$		
SWITCHING CHARACTERISTICS								
Switching Times	t _{on} t _{off}	_ 	82 350	_ _	ns	$I_C = -2A$, $I_{B1} = -200mA$ $I_{B2} = +200mA$, $V_{CC} = -10V$		

Measured under pulsed conditions. Pulse width = $300\mu s$. Duty cycle $\leq 2\%$

Typical Characteristics @T_{amb} = 25°C unless otherwise specified

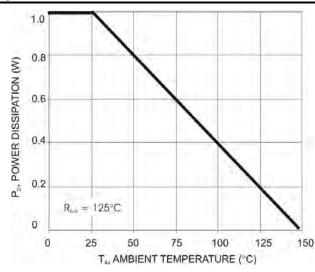


Fig. 1 Power Dissipation vs. Ambient Temperature (Note 3)

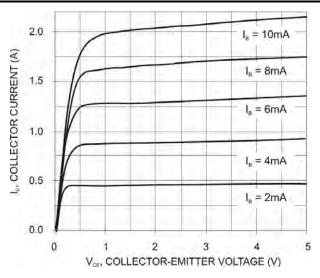
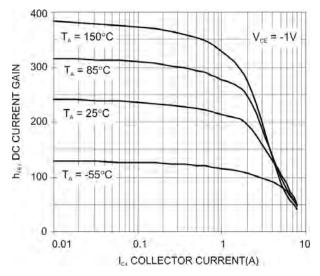
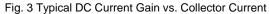


Fig. 2 Collector Current vs. Collector Emitter Voltage







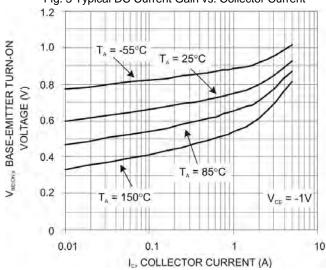


Fig. 5 Base-Emitter Turn-On Voltage vs. Collector Current

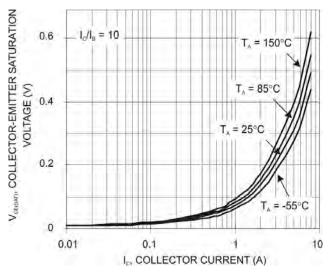


Fig. 4 Collector-Emitter Saturation Voltage vs. Collector Current

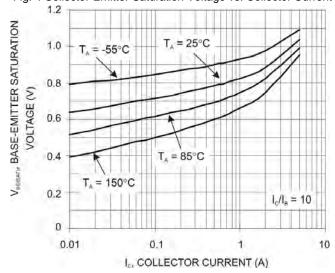


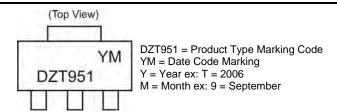
Fig. 6 Base-Emitter Saturation Voltage vs. Collector Current

Ordering Information (Note 5)

Device	Packaging	Shipping
DZT951-13	SOT-223	2500/Tape & Reel

Notes: 5. Packaging Details as shown on page 4, or go to our website at http://www.diodes.com/ap2007.pdf.

Marking Information

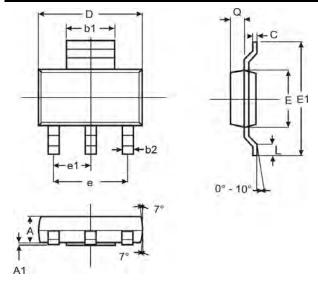


Date Code Key

Year	200	6	2007		2008	20	09	2010		2011	2	2012
Code	Т		U		V	V	V	Χ		Υ		Z
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D

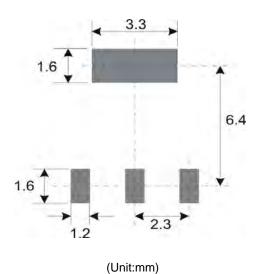


Package Outline Dimensions



SOT-223							
Dim	Min	Max	Тур				
Α	1.55	1.65	1.60				
A 1	0.010	0.15	0.05				
b1	2.90	3.10	3.00				
b2	0.60	0.80	0.70				
С	0.20	0.30	0.25				
D	6.45	6.55	6.50				
Е	3.45	3.55	3.50				
E1	6.90	7.10	7.00				
е		-	4.60				
e1	_		2.30				
L	0.85	1.05	0.95				
Q	0.84	0.94	0.89				
All Dimensions in mm							

Suggested Pad Layout: (Based on IPC-SM-782)



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